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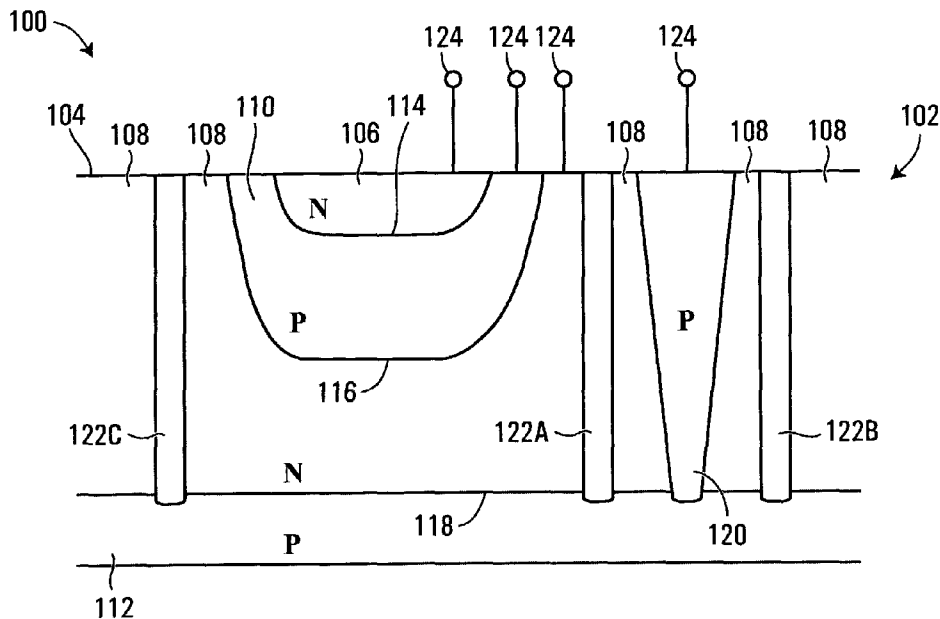
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(54) Title: METHOD AND DEVICE FOR WAVELENGTH-SENSITIVE PHOTO-SENSING USING MULTIPLE PN-JUNCTION



(57) Abstract: A photo-sensing cell (100) having vertically-stacked pn junctions (114, 116, 118) can include one or more insulation regions (122A, 122B, 122C) for laterally isolating adjacent regions in the cell and/or for laterally isolating the cell from an adjacent cell. The photo-sensing cell can be used alone or in an array of cells such as for forming light sensing pixels in a color sensing device. The sensing cell can be formed primarily by epitaxial growth to achieve good control of layer thickness, doping level and doping profile, and well-defined pn junctions.

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